



BUZ11

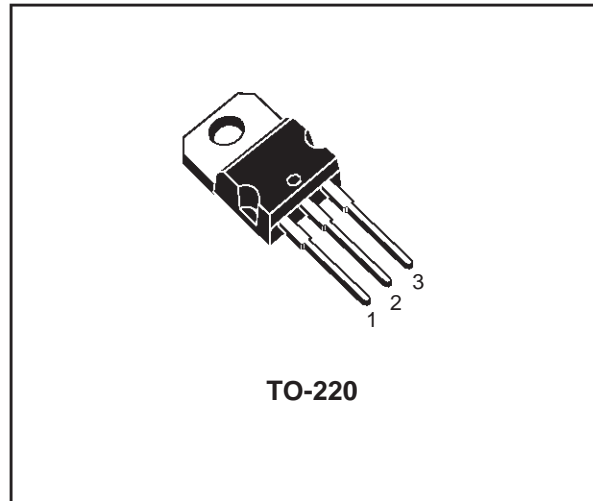
N - CHANNEL 50V - 0.03Ω - 33A TO-220 STripFET™ MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
BUZ11	50 V	< 0.04 Ω	33 A

- TYPICAL R_{DS(on)} = 0.03 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- HIGH CURRENT CAPABILITY
- 175°C OPERATING TEMPERATURE

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- REGULATORS
- DC-DC & DC-AC CONVERTERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- AUTOMOTIVE ENVIRONMENT (INJECTION, ABS, AIR-BAG, LAMPDRIVERS, Etc.)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	50	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	50	V
V _{GS}	Gate-source Voltage	± 20	V
I _D	Drain Current (continuous) at T _c = 25 °C	33	A
I _{DM}	Drain Current (pulsed)	134	A
P _{tot}	Total Dissipation at T _c = 25 °C	90	W
T _{stg}	Storage Temperature	-65 to 175	°C
T _j	Max. Operating Junction Temperature	175	°C
	DIN HUMIDITY CATEGORY (DIN 40040)	E	
	IEC CLIMATIC CATEGORY (DIN IEC 68-1)	55/150/56	

First digit of the datecode being Z or K identifies silicon characterized in this datasheet.